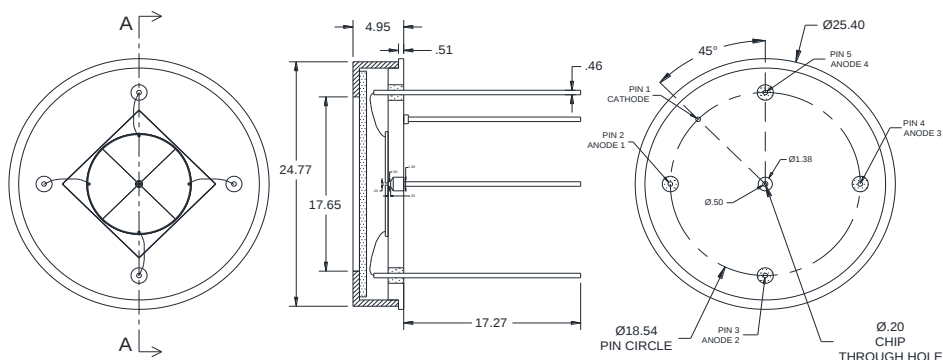


Package dimensions in mm. Chips are centered in reference to package within +/- 0.1 mm



APPLICATIONS

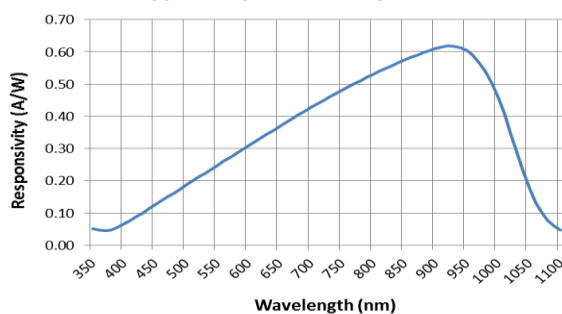
- Backscatter detector for reflectivity measurements

Actual unit may differ.

FEATURES

- 350-1100nm Range
- Quadrant Detector
- $\phi 200\mu\text{m}$ laser cut hole on chip
- Annular package design ideal for coupling with LC ferrule

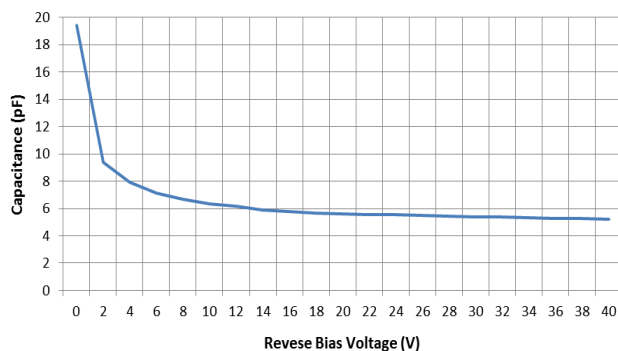
Typical Spectral Response



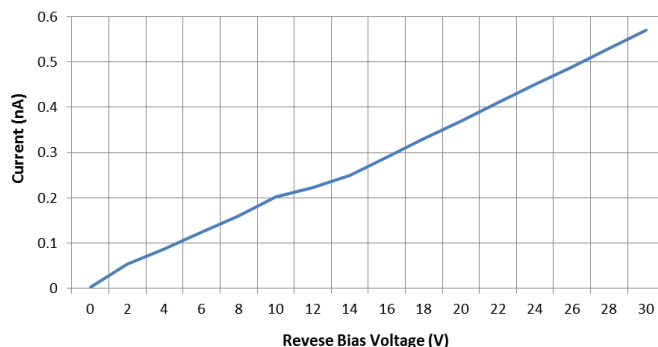
Typical Electro-Optical Specifications @ 23°C, per channel, unless otherwise specified

Parameters	Condition	Min	Typ	Max	Unit
Active Area Dimensions (All Four Quads)			Ø 10		mm
Active Area Per Element			19.5		mm ²
Element Gap			0.014		mm
Responsivity	@ $\lambda=790\text{nm}$		0.55		A/W
Capacitance	@ $V_R=10\text{V}$		60		pF
Dark Current	@ $V_R=10\text{V}$		0.5	10	nA
Reverse Voltage				30	V
Rise Time	@ $V_R=10\text{V}$, $\lambda=780\text{nm}$, $R_L=50\Omega$		6		ns
Noise Equivalent Power	@ $V_R=10\text{V}$, $\lambda=970\text{nm}$		1.9e-14		W/ $\sqrt{\text{Hz}}$
Operating Temperature		-20		+60	°C
Storage Temperature		-20		+80	°C

Capacitance vs. Bias Voltage



Current vs. Bias Voltage



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